EE2026 Tutorial 3 - Solutions

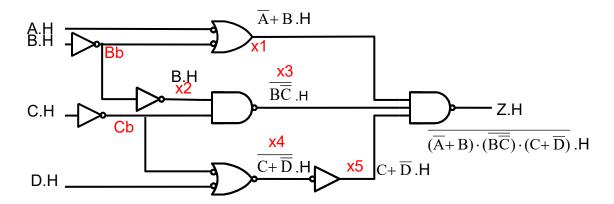
Logic gates

1.
$$F=$$
 $x_1x_3 + x_1\overline{x}_2 + \overline{x}_1x_2x_3 + \overline{x}_1\overline{x}_2\overline{x}_3$
 $= x_3(x_1 + \overline{x}_1x_2) + \overline{x}_2(x_1 + \overline{x}_1\overline{x}_3)$
 $= x_3(x_1 + x_2) + \overline{x}_2(x_1 + \overline{x}_3) \{ \text{using A} + \overline{A} B = A + B \}$
 $= x_1x_3 + x_2x_3 + x_1\overline{x}_2 + \overline{x}_2\overline{x}_3$
 $= x_1x_3 + x_2x_3 + \overline{x}_2\overline{x}_3 \{ \text{using AB} + \overline{A} C + B C = A B + \overline{A} C; A \to x_3, B \to x_1, C \to \overline{x}_2 \}$
or $x_1\overline{x}_2 + x_2x_3 + \overline{x}_2\overline{x}_3 \{ \text{using AB} + \overline{A} C + B C = A B + \overline{A} C; A \to \overline{x}_2, B \to x_1, C \to x_3 \}$

The Verilog module of the original function is as follows (in practical cases, the simplified version will be derived automatically by the synthesis tool, as will be shown in lab sessions):

2. Express all inputs and outputs as active high (i.e., complement active-low signals). The resulting circuit is in positive logic, and the expression of all intermediate nodes x1...x5 is found immediately by proceeding from inputs to output:

Circuit 1



From inspection of the above gate-level structure, the Verilog structural description is:

```
module func(Z,A,B,C,D); // Bb and Cb are complemented (active-low)
input A, B, C, D;
output Z;
wire x1, x2, x3, x4, x5, Bb, Cb; // need to define intermediate wires
not u1(Bb,B); // inverter gate to generate Bb=NOT(B) (omitted inverter)
not u2(Cb,C); // inverter gate to generate Cb=NOT(C) (omitted inverter)
nand u3(x1,A,Bb); // NAND2 gate, instance u3 (push bubbles in gate @top-left)
not u4(x2,Bb); // inverter gate
nand u5(x3,x2,Cb); // NAND2 gate
and u6(x4,Cb,d); // AND2 gate (push bubbles in gate at bottom-left)
not u7(x5,x4); // inverter gate
nand u8(Z,x1,x3,x5); // NAND3 gate
```

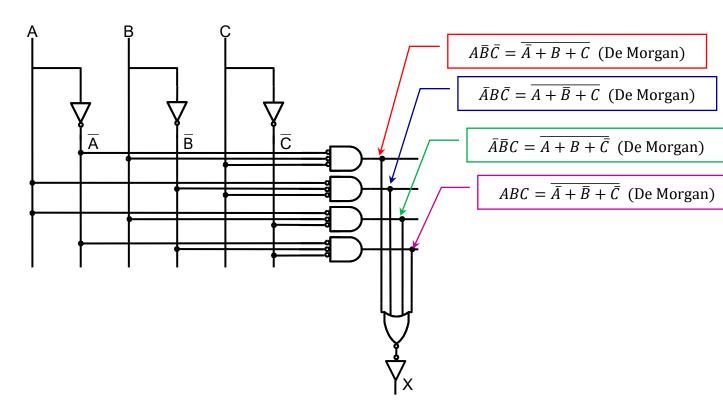
endmodule

A.H B.H C.H Cb Db \overline{C} C.H \overline{A} \overline{A} \overline{C} A.H \overline{A} \overline{A} \overline{C} A.H \overline{A} \overline{A} \overline{C} A.H \overline{A} \overline{A} \overline{C} A.H \overline{C} A.H

From inspection of the above gate-level structure, the Verilog structural description is:

```
module func(Z,A,B,C,D); // Cb and Db are complemented (active-low)
input A, B, C, D;
output Z;
wire x1, x2, x3, Cb, Db;
not u1(Cb,C); // inverter gate to generate Cb=NOT(C) (see omitted inverter)
not u2(Db,D); // inverter gate to generate Db=NOT(D) (see omitted inverter)
nor u3(x1,A,B,Db); // NOR3 gate, instance u3
not u4(x2,A); // inverter gate
nand u5(x3,x2,Cb); // NAND2 gate
nand u6(Z,x1,x3); // NAND2 gate
endmodule
```

3. $X = A \oplus B \oplus C = (A\overline{B} + \overline{A}B) \cdot \overline{C} + \overline{A}\overline{B} + \overline{A}B \cdot C = A\overline{B}\overline{C} + \overline{A}B\overline{C} + \overline{A}B\overline{C} + \overline{A}BC + \overline{A}BC$

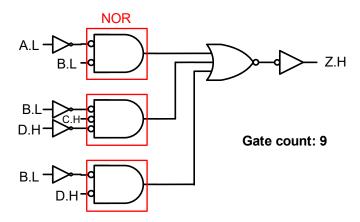


The dataflow Verilog description of the above function $X = A \oplus B \oplus C$ is:

Can you write the structural Verilog description, based on the above gate-level structure?

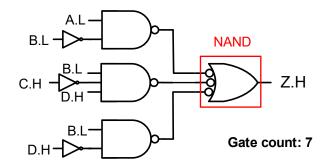
4.
$$\mathbf{Z} = \overline{\mathbf{A}} \mathbf{B} + \overline{\mathbf{B}} \overline{\mathbf{C}} \mathbf{D} + \overline{\mathbf{B}} \overline{\mathbf{D}}$$
 (A, B are active low)

Using NOR gate:



All NOR gates + Not gates (inverters)

Using NAND gate:



All NAND gates + Not gates (inverters)

The dataflow Verilog description of the original function is:

```
\label{eq:module} \begin{split} & \textbf{module} \ func(Z,A,B,C,D); \\ & \textbf{input} \ A, \ B, \ C, \ D; \\ & \textbf{output} \ Z; \\ & \textbf{assign} \ Z = A \ \& \ \sim\! B \ \mid B \ \& \ \sim\! C \ \& \ D \mid B \ \& \ \sim\! D; \ /\!/ \ A, \ B \ were \ complemented \ (active \ low) \\ & \textbf{endmodule} \end{split}
```

Can you describe it in a structural style, starting from the gate-level implementation shown above?